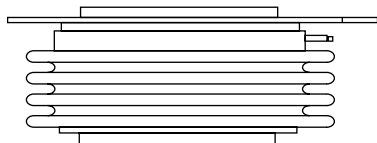


## Phase Control Thyristors (Hockey PUK Version), 1745 A



A-24 (K-PUK)

### FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- Lead (Pb)-free
- Designed and qualified for industrial level


**RoHS**  
COMPLIANT

### PRODUCT SUMMARY

|             |        |
|-------------|--------|
| $I_{T(AV)}$ | 1745 A |
|-------------|--------|

### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

### MAJOR RATINGS AND CHARACTERISTICS

| PARAMETER         | TEST CONDITIONS | VALUES      | UNITS             |
|-------------------|-----------------|-------------|-------------------|
| $I_{T(AV)}$       |                 | 1745        | A                 |
|                   | $T_{hs}$        | 55          | °C                |
| $I_{T(RMS)}$      |                 | 3200        | A                 |
|                   | $T_{hs}$        | 25          | °C                |
| $I_{TSM}$         | 50 Hz           | 33 500      | A                 |
|                   | 60 Hz           | 35 100      |                   |
| $I^2t$            | 50 Hz           | 5615        | kA <sup>2</sup> s |
|                   | 60 Hz           | 5126        |                   |
| $V_{DRM}/V_{RRM}$ |                 | 800 to 1600 | V                 |
| $t_q$             | Typical         | 200         | μs                |
| $T_J$             |                 | - 40 to 125 | °C                |

### ELECTRICAL SPECIFICATIONS

#### VOLTAGE RATINGS

| TYPE NUMBER | VOLTAGE CODE | $V_{DRM}/V_{RRM}$ , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE<br>V | $V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE<br>V | $I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM<br>mA |
|-------------|--------------|------------------------------------------------------------------------|------------------------------------------------------|--------------------------------------------------------|
| ST1230C..K  | 08           | 800                                                                    | 900                                                  | 100                                                    |
|             | 12           | 1200                                                                   | 1300                                                 |                                                        |
|             | 14           | 1400                                                                   | 1500                                                 |                                                        |
|             | 16           | 1600                                                                   | 1700                                                 |                                                        |

| ABSOLUTE MAXIMUM RATINGS                                 |                     |                                                                                                           |                                  |                                                                       |            |                    |
|----------------------------------------------------------|---------------------|-----------------------------------------------------------------------------------------------------------|----------------------------------|-----------------------------------------------------------------------|------------|--------------------|
| PARAMETER                                                | SYMBOL              | TEST CONDITIONS                                                                                           |                                  |                                                                       | VALUES     | UNITS              |
| Maximum average on-state current at heatsink temperature | I <sub>T(AV)</sub>  | 180° conduction, half sine wave double side (single side) cooled                                          |                                  |                                                                       | 1745 (700) | A                  |
|                                                          |                     |                                                                                                           |                                  |                                                                       | 55 (85)    | °C                 |
| Maximum RMS on-state current                             | I <sub>T(RMS)</sub> | DC at 25 °C heatsink temperature double side cooled                                                       |                                  |                                                                       | 3200       | A                  |
| Maximum peak, one-cycle non-repetitive surge current     | I <sub>TSM</sub>    | t = 10 ms                                                                                                 | No voltage reapplied             | Sinusoidal half wave, initial T <sub>J</sub> = T <sub>J</sub> maximum | 33 500     |                    |
|                                                          |                     | t = 8.3 ms                                                                                                |                                  |                                                                       | 35 100     |                    |
|                                                          |                     | t = 10 ms                                                                                                 | 100 % V <sub>RRM</sub> reapplied |                                                                       | 28 200     |                    |
|                                                          |                     | t = 8.3 ms                                                                                                |                                  |                                                                       | 29 500     |                    |
| Maximum I <sup>2</sup> t for fusing                      | I <sup>2</sup> t    | t = 10 ms                                                                                                 | No voltage reapplied             |                                                                       | 5615       | kA <sup>2</sup> s  |
|                                                          |                     | t = 8.3 ms                                                                                                |                                  |                                                                       | 5126       |                    |
|                                                          |                     | t = 10 ms                                                                                                 | 100 % V <sub>RRM</sub> reapplied |                                                                       | 3971       |                    |
|                                                          |                     | t = 8.3 ms                                                                                                |                                  |                                                                       | 3625       |                    |
| Maximum I <sup>2</sup> √t for fusing                     | I <sup>2</sup> √t   | t = 0.1 to 10 ms, no voltage reapplied                                                                    |                                  |                                                                       | 56 150     | kA <sup>2</sup> √s |
| Low level value of threshold voltage                     | V <sub>T(TO)1</sub> | (16.7 % × π × I <sub>T(AV)</sub> ) < I < π × I <sub>T(AV)</sub> , T <sub>J</sub> = T <sub>J</sub> maximum |                                  |                                                                       | 0.93       | V                  |
| High level value of threshold voltage                    | V <sub>T(TO)2</sub> | (I > π × I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum                                    |                                  |                                                                       | 1.02       |                    |
| Low level value of on-state slope resistance             | r <sub>t1</sub>     | (16.7 % × π × I <sub>T(AV)</sub> ) < I < π × I <sub>T(AV)</sub> , T <sub>J</sub> = T <sub>J</sub> maximum |                                  |                                                                       | 0.17       | mΩ                 |
| High level value of on-state slope resistance            | r <sub>t2</sub>     | (I > π × I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum                                    |                                  |                                                                       | 0.16       |                    |
| Maximum on-state voltage                                 | V <sub>TM</sub>     | I <sub>pk</sub> = 4000 A, T <sub>J</sub> = T <sub>J</sub> maximum, t <sub>p</sub> = 10 ms sine pulse      |                                  |                                                                       | 1.62       | V                  |
| Maximum holding current                                  | I <sub>H</sub>      | T <sub>J</sub> = 25 °C, anode supply 12 V resistive load                                                  |                                  |                                                                       | 600        | mA                 |
| Typical latching current                                 | I <sub>L</sub>      |                                                                                                           |                                  |                                                                       | 1000       |                    |

| SWITCHING                                                |         |                                                                                                                                                                                   |        |       |
|----------------------------------------------------------|---------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------|-------|
| PARAMETER                                                | SYMBOL  | TEST CONDITIONS                                                                                                                                                                   | VALUES | UNITS |
| Maximum non-repetitive rate of rise of turned-on current | $di/dt$ | Gate drive 20 V, 20 Ω, $t_r \leq 1 \text{ μs}$<br>$T_J = T_J \text{ maximum}$ , anode voltage $\leq 80 \% V_{DRM}$                                                                | 1000   | A/μs  |
| Typical delay time                                       | $t_d$   | Gate current 1 A, $di_g/dt = 1 \text{ A/μs}$<br>$V_d = 0.67 \% V_{DRM}$ , $T_J = 25 \text{ °C}$                                                                                   | 1.9    | μs    |
| Typical turn-off time                                    | $t_q$   | $I_{TM} = 550 \text{ A}$ , $T_J = T_J \text{ maximum}$ , $di/dt = 40 \text{ A/μs}$ ,<br>$V_R = 50 \text{ V}$ , $dV/dt = 20 \text{ V/μs}$ , gate 0 V 100 Ω, $t_p = 500 \text{ μs}$ | 200    |       |

| BLOCKING                                           |                          |                                                               |        |       |
|----------------------------------------------------|--------------------------|---------------------------------------------------------------|--------|-------|
| PARAMETER                                          | SYMBOL                   | TEST CONDITIONS                                               | VALUES | UNITS |
| Maximum critical rate of rise of off-state voltage | $dV/dt$                  | $T_J = T_J \text{ maximum}$ linear to 80 % rated $V_{DRM}$    | 500    | V/μs  |
| Maximum peak reverse and off-state leakage current | $I_{RRM}$ ,<br>$I_{DRM}$ | $T_J = T_J \text{ maximum}$ , rated $V_{DRM}/V_{RRM}$ applied | 100    | mA    |



| TRIGGERING                          |                    |                                                                |                                                                                                                                                                    |        |      |       |
|-------------------------------------|--------------------|----------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------|------|-------|
| PARAMETER                           | SYMBOL             | TEST CONDITIONS                                                |                                                                                                                                                                    | VALUES |      | UNITS |
|                                     |                    |                                                                |                                                                                                                                                                    | TYP.   | MAX. |       |
| Maximum peak gate power             | P <sub>GM</sub>    | T <sub>J</sub> = T <sub>J</sub> maximum, t <sub>p</sub> ≤ 5 ms |                                                                                                                                                                    | 16     |      | W     |
| Maximum average gate power          | P <sub>G(AV)</sub> | T <sub>J</sub> = T <sub>J</sub> maximum, f = 50 Hz, d% = 50    |                                                                                                                                                                    | 3      |      |       |
| Maximum peak positive gate current  | I <sub>GM</sub>    | T <sub>J</sub> = T <sub>J</sub> maximum, t <sub>p</sub> ≤ 5 ms |                                                                                                                                                                    | 3.0    |      | A     |
| Maximum peak positive gate voltage  | + V <sub>GM</sub>  |                                                                |                                                                                                                                                                    | 20     |      | V     |
| Maximum peak negative gate voltage  | - V <sub>GM</sub>  |                                                                |                                                                                                                                                                    | 5.0    |      |       |
| DC gate current required to trigger | I <sub>GT</sub>    | T <sub>J</sub> = - 40 °C                                       | Maximum required gate trigger/<br>current/voltage are the lowest<br>value which will trigger all units<br>12 V anode to cathode applied                            | 200    | -    | mA    |
|                                     |                    | T <sub>J</sub> = 25 °C                                         |                                                                                                                                                                    | 100    | 200  |       |
|                                     |                    | T <sub>J</sub> = 125 °C                                        |                                                                                                                                                                    | 50     | -    |       |
| DC gate voltage required to trigger | V <sub>GT</sub>    | T <sub>J</sub> = - 40 °C                                       |                                                                                                                                                                    | 1.4    | -    | V     |
|                                     |                    | T <sub>J</sub> = 25 °C                                         |                                                                                                                                                                    | 1.1    | 3.0  |       |
|                                     |                    | T <sub>J</sub> = 125 °C                                        |                                                                                                                                                                    | 0.9    | -    |       |
| DC gate current not to trigger      | I <sub>GD</sub>    | T <sub>J</sub> = T <sub>J</sub> maximum                        | Maximum gate current/<br>voltage not to trigger is the<br>maximum value which will not<br>trigger any unit with rated V <sub>DRM</sub><br>anode to cathode applied | 10     |      | mA    |
| DC gate voltage not to trigger      | V <sub>GD</sub>    |                                                                |                                                                                                                                                                    | 0.25   |      | V     |

| THERMAL AND MECHANICAL SPECIFICATIONS            |              |                                               |  |                  |           |
|--------------------------------------------------|--------------|-----------------------------------------------|--|------------------|-----------|
| PARAMETER                                        | SYMBOL       | TEST CONDITIONS                               |  | VALUES           | UNITS     |
| Maximum operating junction temperature range     | $T_J$        |                                               |  | - 40 to 125      | °C        |
| Maximum storage temperature range                | $T_{Stg}$    |                                               |  | - 40 to 150      |           |
| Maximum thermal resistance, junction to heatsink | $R_{thJ-hs}$ | DC operation single side cooled               |  | 0.042            | K/W       |
|                                                  |              | DC operation double side cooled               |  | 0.021            |           |
| Maximum thermal resistance, case to heatsink     | $R_{thC-hs}$ | DC operation single side cooled               |  | 0.006            |           |
|                                                  |              | DC operation double side cooled               |  | 0.003            |           |
| Mounting force, $\pm 10$ %                       |              |                                               |  | 24 500<br>(2500) | N<br>(kg) |
| Approximate weight                               |              |                                               |  | 425              | g         |
| Case style                                       |              | See dimensions - link at the end of datasheet |  | A-24 (K-PUK)     |           |

| $\Delta R_{thJC}$ CONDUCTION |                       |             |                        |             |                     |       |
|------------------------------|-----------------------|-------------|------------------------|-------------|---------------------|-------|
| CONDUCTION ANGLE             | SINUSOIDAL CONDUCTION |             | RECTANGULAR CONDUCTION |             | TEST CONDITIONS     | UNITS |
|                              | SINGLE SIDE           | DOUBLE SIDE | SINGLE SIDE            | DOUBLE SIDE |                     |       |
| 180°                         | 0.003                 | 0.003       | 0.002                  | 0.002       | $T_J = T_J$ maximum | K/W   |
| 120°                         | 0.004                 | 0.004       | 0.004                  | 0.004       |                     |       |
| 90°                          | 0.005                 | 0.005       | 0.005                  | 0.005       |                     |       |
| 60°                          | 0.007                 | 0.007       | 0.007                  | 0.007       |                     |       |
| 30°                          | 0.012                 | 0.012       | 0.012                  | 0.012       |                     |       |

**Note**

- The table above shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC

# ST1230C..KP Series

Vishay High Power Products Phase Control Thyristors  
(Hockey PUK Version), 1745 A

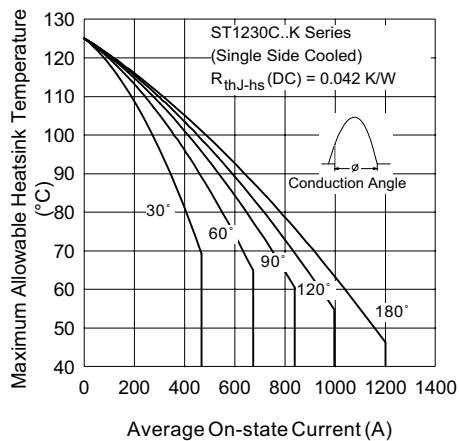


Fig. 1 - Current Ratings Characteristics

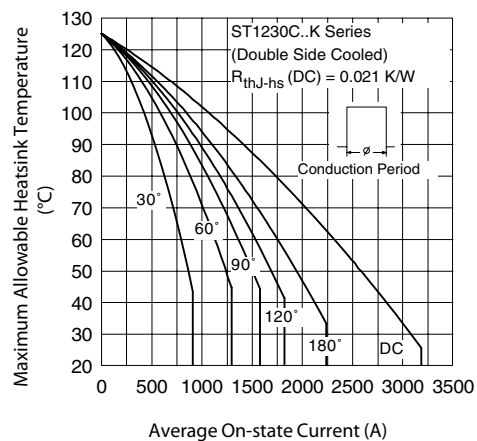


Fig. 4 - Current Ratings Characteristics

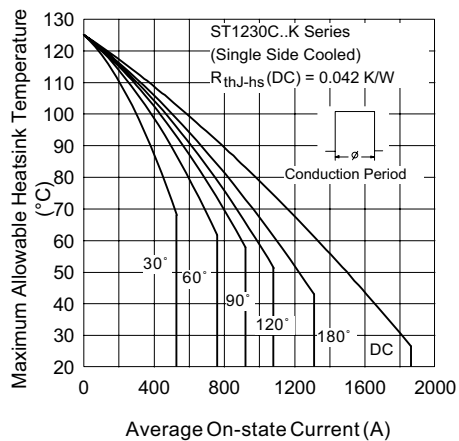


Fig. 2 - Current Ratings Characteristics

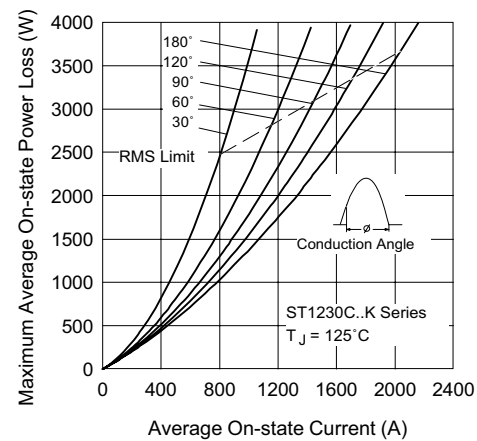


Fig. 5 - On-State Power Loss Characteristics

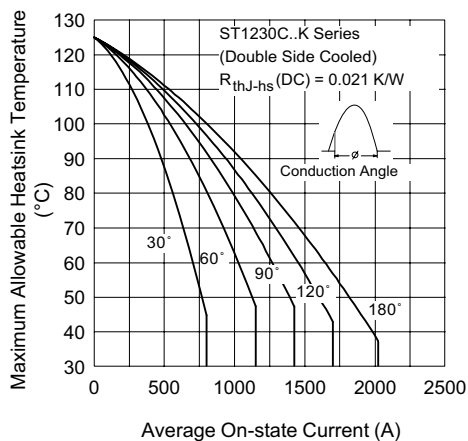


Fig. 3 - Current Ratings Characteristics

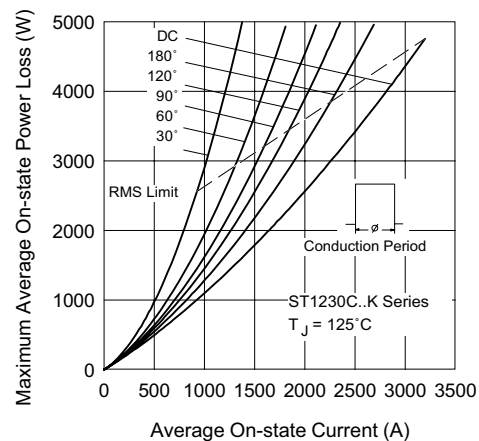


Fig. 6 - On-State Power Loss Characteristics

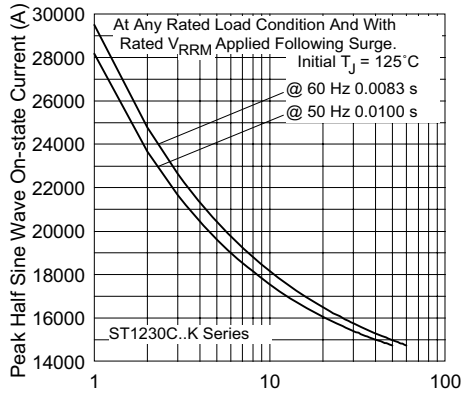


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

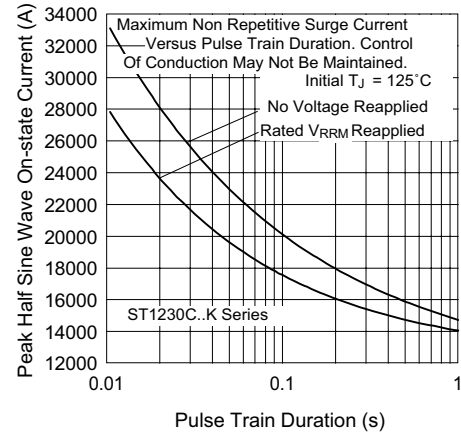


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

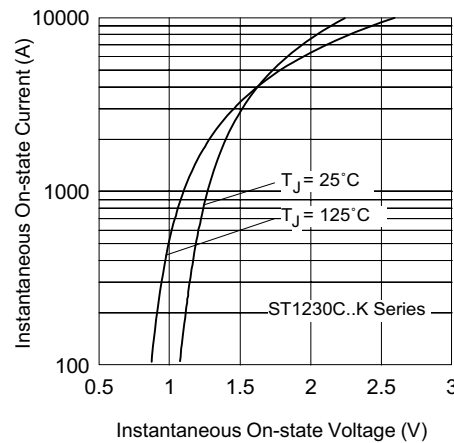


Fig. 9 - On-State Voltage Drop Characteristics

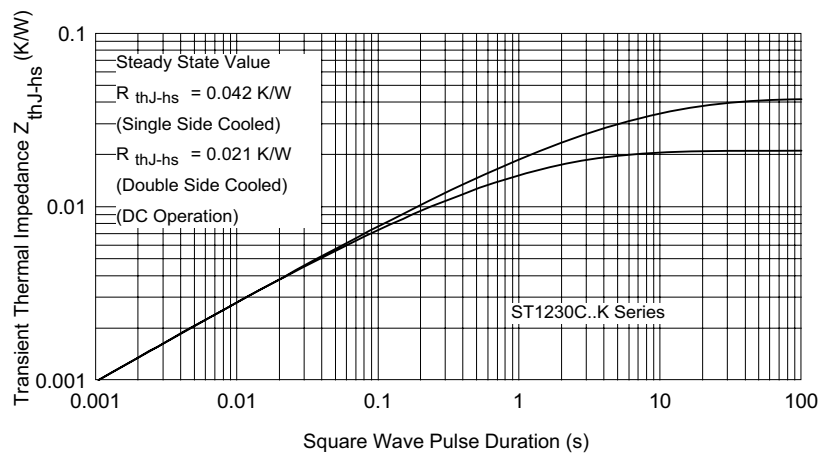


Fig. 10 - Thermal Impedance  $Z_{thJ-hs}$  Characteristics

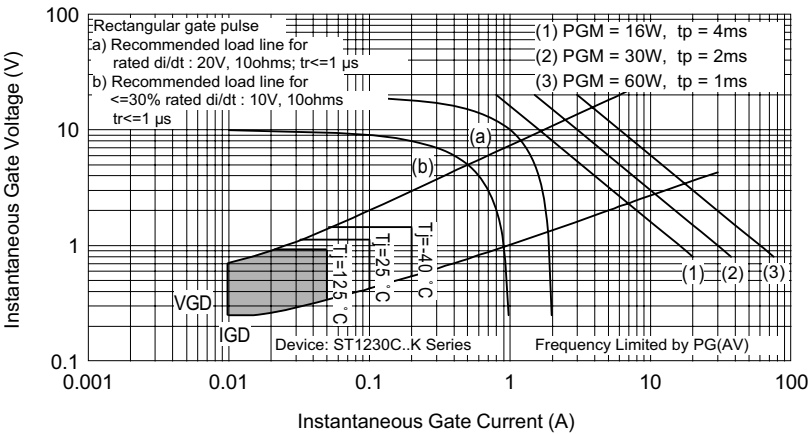


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

|             |    |     |   |   |    |   |   |   |   |
|-------------|----|-----|---|---|----|---|---|---|---|
| Device code | ST | 123 | 0 | C | 16 | K | 1 | - | P |
|             | 1  | 2   | 3 | 4 | 5  | 6 | 7 | 8 | 9 |

- 1 - Thyristor
- 2 - Essential part number
- 3 - 0 = Converter grade
- 4 - C = Ceramic PUK
- 5 - Voltage code x 100 =  $V_{RRM}$  (see Voltage Ratings table)
- 6 - K = PUK case A-24 (K-PUK)
- 7 - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)  
1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)  
2 = Eyelet terminals (gate and auxiliary cathode soldered leads)  
3 = Fast-on terminals (gate and auxiliary cathode soldered leads)
- 8 - Critical dV/dt : • None = 500 V/ $\mu$ s (standard selection)  
• L = 1000 V/ $\mu$ s (special selection)
- 9 - Lead (Pb)-free

| LINKS TO RELATED DOCUMENTS |                                                                               |
|----------------------------|-------------------------------------------------------------------------------|
| Dimensions                 | <a href="http://www.vishay.com/doc?95081">http://www.vishay.com/doc?95081</a> |



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- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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